## LBI-38531B

## MAINTENANCE MANUAL 136-174 MHz, 110 WATT POWER AMPLIFIER 19D902797G1

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## DESCRIPTION

The VHF Power Amplifier Assembly is a wide band RF power amplifier operating over the entire 136 to 174 MHz range without tuning or band splitting. Its main function is to amplify the 10 mW FM signal from the Transmitter Synthesizer to the rated RF output of 110 watts at the antenna port. The output of the Power Amplifier Assembly is adjustable from 65 to 135 watts at the PA output J104. This corresponds to a rated RF output of 55 to 110 watts at the antenna.

The assembly consists of a printed wiring board (A1) and associated components, including a power module and three RF power transistors, mounted to the heat sink assembly. The printed wiring board (A1) contains both the power amplifier circuitry (100 series components) and the power control circuitry (200 series components).

Unfiltered supply voltage, A+, for the power amplifier circuits enters the assembly via feedthrough capacitor, C1. Power cable W4 routes the A+ from CI to J103 on the PWB. Filtered A+ voltage for the power control circuit enters the assembly via control cable W13 which connects to the PWB at J201.

The Power Control circuitry sets the output power level by adjusting the PA Power Set level. It keeps the output power constant despite variations in input power, power amplifier gain, or temperature through the use of a feedback control loop in the PA assembly.

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TABLE 1 - GENERAL SPECIFICATIONS			
ITEM	SPECIFICATION		
FREQUENCY	136 MHz - 174 MHz		
OUTPUT POWER	65 watts - 135 watts (into Low Pass Filter)		
INPUT POWER (RF)	10 mW min. into 2:1 VSWR		
TEMPERATURE RANGE	30°C TO + 60°C (Ambient air)		
SUPPLY VOLTAGE	13.4 Vdc		
CURRENT	29 Amps max. (25 A typical @ 135W, 13.4V)		
DUTY CYCLE	Continous		
STABILITY	Stable into 3:1 VSWR; all temp. ,voltage, freq. 65 watts - 135 watts		
RUGGEDNESS AT HIGH VSWR	No damage into open or short load.		

#### **CIRCUIT ANALYSIS**

#### **POWER AMPLIFIER**

The power amplifier section of the PA Board consists of an Exciter, a Low Level Amplifier, a Driver, and the Power Amplifier Finals. All these gain stages have an input and output impedance of 50 ohms. Figure 1 is a block diagram showing the signal flow within the Power Amplifier Assembly.

#### Exciter (UIOI)

The Exciter stage uses a broadband silicon monolithic microwave integrated circuit (MMIC) amplifier. The signal from transmitter synthesizer, typically 10 dBm (10 mW), is input to the Exciter through a 10 dB resistive pad (R100R102). The Exciter amplifies the resulting 0 dBm (1 mW) signal to 20 dBm (100 mW). Following the Exciter is a 3 dB resistive pad (R104R106). This attenuatorreduces the MMIC output power to 17 dBm (50 mW).

The MMIC requires a 5 volt supply source. The 8 volt regulator (U100) provides the 5 volts to the MMIC via a dropping resistor R103.

#### Low Level Amplifier (U1O2)

The Low Level Amplifier (LLA) stage uses a 50 ohm thick film RF Power Module to amplify and control of the output power. Internally, the module is a two stage amplifier. The power control circuitry controls the gain of the first stage by varying the collector voltage of Q203. The second stage gain remains constant with A + providing the DC supply voltage.

The signal from the Exciter stage, typically 17 dBm (50 mW), is input into the LLA. Under maximum Power Set conditions, the LLA amplifies the signal to a typical output level of 40 dBm (10 W).

#### Driver (Q101)

The driver is a 6 dB RF amplifier. A network consisting of C114C117 and C139 and L103L105 provides interstage impedance matching between U102 and Q101. The signal from the LLA, typically 40 dBm (10 W), is amplified to 46 dBm (40 W). Impedance matching between the driver output and the input to U103 is provided by C145, C148, C152, C153, and L108. The splitter, U103, is a quadrature 90° hybrid coupler. It divides the signal and applies equal power to the two Power Amplifier Finals, Q102 and Q103.



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Figure 1 - Block Diagram

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#### Power Amplifier Finals (Q102, Q103)

Each of the Power Amplifier Final devices is capable of producing 5.5 dB of gain. The output signal from the Splitter is impedance matched to each of the finals. Under optimum conditions each final amplifies the 43 dBm (20 W) power input signal to 48.45 dBm (70 W) output power. The outputs are then impedance matched to the input of the Combiner, U104. The Combiner is a quadrature 90° hybrid coupler which combines (sums) the output power of the finals. This produces an output power of approximately 51.3 dBm (135 W) which is coupled through C 140 to the directional coupler (part of A1 PWB) and on to the antenna circuits. In addition, the directional coupler samples both forward and reverse power and sends this sample to the Power Control circuitry.

#### **POWER CONTROL**

The Power Control circuitry performs three basic functions. It keys and unkeys the PA, sets the PA output power, and protects the PA against adverse conditions.

#### Keying and Unkeying the PA

To key the PA, the digital controller places 5 volts on the PA key line, J201-2. Zero volts on the PA key line causes the PA to unkey. If the control cable (W13) is disconnected, with nothing actively driving the PA key line, the PA will remain unkeyed.

#### **PA Output Power Set**

PA output power is set according to the level of the Power Set line. Four (4) volts on this line will produce minimum power. As the voltage increases toward eight (8) volts, the power will increase to its maximum rated output. The PA output power is initially set for an output of 135 watts at J104. This is done by adjusting R217 while injecting a 10 mW signal at J1 and applying 8 volts to J201-3. After setting the maximum power level, changing the output power is done by varying the voltage applied on the Power Set line.

#### **PA Protection**

The power control also protects the PA against over temperature and high VSWR conditions.

An over temperature condition exists when the flange temperature of the final output transistor reaches  $80^{\circ}$ C. At this point the output power will drop below its set level. The output power will continue to drop such that when the flange temperature reaches  $125^{\circ}$ C the PA output drops at least 10 dB below its set level.

Reflected power is limited to 25% of the set power. If the output VSWR degrades to worse than 3:1 the forward power will be reduced to limit the reflected power to 25% of the set power. The Power Sensor line indicates when the PA is operating in a cutback condition. If the PA is keyed and the power control is cutting back, the Power Sensor line will drop to zero (0) volts and the PA alarm light on the station will turn on.

#### **Theory of Operation**

Power control of the MASTR III Power Amplifier is accomplished with a feedback control loop. The three possible feedback signals are: representation of forward power, temperature sensitive scaled representation of forward power, or representation of reflected power. These three signals are input to a diode summing junction which selects the largest of the three for use as the feedback.

The stripline directional coupler samples the output power and produces a voltage, Vf, proportional to the forward output power. The power control compares the forward voltage, Vf, to a reference voltage at U201D. The output of U201D controls the current flow thru Q202 and the output of Q203. The collector output of Q203 adjusts the control voltage, Vct1. This control voltage is capable of adjusting the total PA output power since it provides the first stage DC supply to the Low Level Amplifier, U102.

During over temperature operation, a scaled representation of the forward power is maintained constant by varying the control voltage line. Thermal resistor R209 sensing an increase in temperature causes the output of U201A to increase. If the output of U201A becomes larger than the other feedback lines, the output of U201D will begin to decrease. This in turn will cause the output of Q203 to decrease reducing the supply voltage to U102. Since the scaling is a function of temperature the power is reduced as the temperature increases.

Under VSWR cutback operation the reverse voltage, Vr, representative of the reflected output power is held below a threshold by reducing the control voltage as necessary. If Vr increases at U201B beyond the preset threshold an increase at U201D will result. This causes a subsequent reduction in the control voltage to U102. Thus the power control circuit reduces the output power in order to limit the reflected power to 25% of the set power.

#### **Signal Interface**

The signal interface to the MASTR III Power Amplifier is supported by a six position feedthrough connector, J201, with the following pinout:

- 1 POWER SENSE
- 2 PA Key
- 3 POWER SET
- 4 NC
- 5 Ground
- 6 13.8 VF

#### **Power Sense**

This line indicates when the PA is experiencing adverse conditions. Under normal operation, while the PA is keyed, this line will be proportional to forward power. Minimum power (zero watts) corresponds to 2.5 volts while maximum power corresponds to 4.5 volts. This voltage is not temperature compensated and no effort is made to calibrate this signal to an absolute power level. It is intended to provide a relative indication of forward power and to discriminate between normal and cutback operation.

Zero volts on this line, when the PA is keyed, indicates the forward power is cutback. This power cutback may be due to high reflected power (VSWR) or may be due to high PA temperatures. This fault condition may indicate a problem with the PA or may indicate a system problem external to the Power Amplifier. High VSWR may be due to a poor antenna and high temperature may be due to a blocked cabinet vent. Zero volts on this line, when the PA is keyed, does not indicate zero forward power. Zero volts indicates the PA is protecting itself due to adverse conditions. If the adverse condition, either high VSWR or high temperature is eliminated, the power will return to normal and the PWR SENSOR voltage will rise above 2.5 volts.

#### PA Key (Interface Connector pin 2)

This line is used to key and unkey the PA. UNKEY = 0 volt and KEY = 5 volts. The driver of this line must be capable of supplying 5 volts at 1.0 mA. The appropriate key sequence requires RF from the transmit synthesizer be input to the PA before the KEY line is energized.

#### **Power Set (Interface Connector pin 3)**

This line is used to set the RF Power Output of the PA. Minimum power output equals 4 volts and maximum power output equals 8 volts. The driver of this line must be capable of supplying 8 volts at 1.0 mA.

#### 13.8 VF (Interface Connector pin 6)

This line provides the filtered supply voltage for the Power Control. The driver of this line must be capable of supplying 13.8 volts  $\pm 20\%$  at 100 mA.

## **TROUBLESHOOTING GUIDE**

SYMPTOM	AREAS TO CHECK	INDICATIONS
1. No Power or low Power at Antenna Port	1. Measure the transmitter output power before the duplexer or antenna switch (for simplex mode).	The presence of power at this port is an indication of a defective duplexer, switch, or cables.
	2. Measuer the transmitter output power before the low pass filter.	The presence of power at this port is an indication of a defective filter or cables.
	3. Measure the transmitter output power before the optional isolator at the PA output port.	The presence of power at this port is an indication of a defective isolator or cables.
2. No power at PA output port and PA ALARM is OFF	1. Station is in receive mode.	
3. No power at PA output port and PA ALARM is ON.	1. No RF input to PA. Check connection between PA and TX Synthesizer.	TX Synthesizer should deliver a minimum of 10 mW (10 dBm) to the PA.
	2. Check the logic or DC inputs to the PA from the Interface Board through J201.	
	a. J201-2 PA KEY	5 volts during transmit
	b. J201-3 POWER SET	4 volts to 8 volts (4 volts represents zero RF power)
	c. J201-6 13.8 VF	13.8 Vdc ±20%
	3. Defective PA	Replace PA
4. Low power at PA output port and PA ALARM is OFF	1. Low RF input to PA from TX Synthesizer.	Power should be a minimum of 10 mW (10 dBM).
	2. Check the voltage on J201-3 (POWER SET).	For nominal output power, this voltage should be above 6 volts.
	3. Check the power supply voltage on the collector of Q101, Q102 and Q103.	Voltage should be nominal 13.4 Vdc.
	4. One of the two final PA transistors (Q102 or Q103 is defective.	Replace the defective transistor.
5. Low power at PA output port and PA ALARM is ON.	1. Check for over temperature and/or a high VSWR condition due to a mis- match at the output port.	The power control circuit protects the PA by cutting back the power. In case of a mismatch, refer to symptom 1.

## VHF POWER AMPLIFIER VOLTAGE CHART

PARAMETER (50 OHM, -30° TO +60° C)	REFERENCE SYMBOL	READINGS (volts DC)
SUPPLY VOLTAGE	A+	13.4 V ±20%
CONTROL VOLTAGE	Vct 1	0 - 12 V
FORWARD VOLTAGE	Vf	3 - 7 V
REVERSE VOLTAGE	Vr	2 - 6 V
POWER SENSE	J201-1	2.5 - 4 V
РА КЕҮ	J201-2	5 V
POWER SET	J201-3	4 - 8 V
13.8 VF	J201-6	13.8 V ±20%

## VHF POWER AMPLIFIER TYPICAL VOLTAGE READINGS (50 ohm, room temperature, 13.4 Vdc supply voltage, and 110 watt output)

REFERENCE SYMBOL	@ 136 MHz (volts DC)	@ 150 MHz (volts DC)	@ 162 MHz (volts DC)	@ 174 MHz (volts DC)
Vct1	7 - 10 V	6 - 8 V	4 - 6 V	4 - 6 V
Vf	5 - 7 V	5 - 7 V	5 - 7 V	5 - 7 V
Vr	2 - 3 V	2 - 3 V	2 - 3 V	2 - 3 V
J201-1	2.5 - 4 V			
J201-3	6 - 8 V	6 - 8 V	6 - 8 V	6 - 8 V
J201-6	13.4 V	13.4 V	13.4 V	13.4 V

## **RATED POWER FOR MASTR III VHF BASE STATION**

STANDARD	WITH	WITH	WITH DUPLEXER
	DUPLEXER	ISOLATOR	AND ISOLATOR
110W	75W	95W	70W

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## IC DATA



5		5
1 2	3	4

**U102** 19A70532P1 PA AMPLIFIER MODULE

1.	P in	

- 2. Vcci 1ST STAGE
- 3. Vcc FINAL
- 4. Pout
- 5. FIN GROUND

			SYMBOL	ge part no.	DESCRIPTION
	I	10 WATT POWER AMPLIFISE 19D90279701	C170 and C171	19A705205P7	Tantalum: 10 uF, 25 VDCM; sim to Sprague 293D.
		ISSUE 1	C201	19R702051P41	Ceramic: 39 pF ± 5%, 50 VDCW, temp coef 0 ± 30 FFM.
		]	C202 and C203	19R702052P26	Ceramic: 0.1 uF ± 10%, 50 VDCN.
SYMBOL	GE PART NO.	DESCRIPTION	C204	19A702061P41	Ceramic: 39 pP ± 5%, 50 VDCW, temp coef 0 + 30 PPM.
		ASSEMBLIES	C205 thru	19A702052P5	Ceramic: 1000 pF ±104, 50 VDCN.
<b>A</b> 1		POWER ANPLIFIER BOARD 199902794G1	C207 C208	198702052P26	Ceramic: 0.1 uF ± 10%, 50 VDCW.
			C209	19A702052P5	Ceramic: 1000 pF ±10%, 50 VDCW.
C100	10170205205	Comparing Inco	C213	19A702052P26	Ceramic: 0.1 uP ± 10%, 50 VDCW.
and C101	194/0205295	Geramic: 1000 pF ±10%, 50 VDCW.	C225	19A702052P24	Ceramic: 0.068 uF ± 10%, 50 VDCW.
C103	19870205225	Ceramic: 1000 pF +108 50 VDCV	C263	19A702052P5	Ceramic: 1000 pF ±10%, 50 VDCW.
C104	198705108P120	Mica chin: 1000 pF +5%, 100 VDCW	C266	19A702052P5	Ceramic: 1000 pF ±10%, 50 VDCW,
and C105			C270	19A702052P5	Ceramic: 1000 pF ±10%, 50 VDCM.
C106	19A705205P7	Tantalum: 10 uF, 25 VDCN; sim to Sprague 293D.	C272 and	19A702052P5	Ceramic: 1000 pP ±10%, 50 VDCW.
C109	198705205P7	Tantalum: 10 uF, 25 VDCW; sim to Sprague 293D.	C273		
C110	193705108F120	Micz chip: 1000 pF, ±5%, 100 VDCW.			DIODES
c111	19A705205P7	Tantalum: 10 uP, 25 VDGW; sim to Sprague 293D.			
Cl12			and	194700047P3	1987022509113
C114	19A705108F19	Mica: 18 pP ± 5%, 500 VDCW.	0202		
C115	19A705108P40	Mica chip: 91 pF, 15%.	D203	19A700053P3	Silicon: 2 Diodes in Series, Common Cathode;
C116 and C117	19 <b>3705108</b> 995	Capacitor, Mics Chip: 200pF ± 5%, 100 VDCW, temp coef 0 + 50 FPM.	D205 and D204	19A700053F3	Silicon: 2 Diodes in Series, Common Cathode; sim to KBAV70L.
C119	19A705108F22	Mica: 24 pF ± 5%, 500 VDCN.	D200	19870004793	1937072500113
C123	19A705108P22	Mica: 24 pF ± 5%, 500 VDCN.	D210	1987000839102	Silicon: 5.1 Volt Zener: sim to BZX84-C5V1.
C124	197703108P30	Mica: 51 pF ± 5%, 500 VDCH.			
C125	19 <b>3705108</b> P35	Mica: 82 pF ±5%, 500 VDCW, temp coef 0 +50 PPM/*C.	J101	198705512F1	Connector, RF SMB Series: sim to AMP No.
C126	19A705108P30	Nica: 51 pF ± 5%, 500 VDCW.			221111-1.
C128 thru C130	19A705108P35	Nica: 82 pP ±5%, 500 VDCN, temp coef 0 +50 PPM/°C.	J103 J201	198702778P464 198704852P32	Threaded metalic spacer, swage type. Printed wire, two part: 6 contacts, sim to Nolex
C131 and C132	344A3126P41	Porcelian: 130 pP ±5%, 300 VDCW,			22-29-2051.
C133	19A7051089120	Mica chip: 1000 pF, ±5%, 100 VDCW.	L100	19A70109101	Coil.
and C134			L101	19870109101	Coil.
C135	344A3126P41	Porcelian: 130 pF ±5%, 300 VDCN.	L102	19A129569P1	Coil.
810 C136			L103	19A701418P1	Coil.
C137	19A705108P120	Mica chip: 1000 pF, 15%, 100 VDCW.	L104	19A701420P5	Coil.
C138			L105	198701091G1	Coil.
C139	19A705108P33	Mica chip: 68 pF, ±5%, 100 VDCW.	LIDE	19A129569P1	Coil.
c140 and	19A705108P120	Mica chip: 1000 pP, ±5%, 100 VDCW.	L108	198701418P1	Coil.
C141 C145	19A705108F25	Mica Chip: 33 pF 15%, 500 VDCW. temp cosf	L115 L116	19A701418P1 19A701420P5	Coil. Coil.
		0 + 50 PPH/'C.	L117	198701418P1	Coil.
C147	19A705108P120	Mica chip: 1000 pF, ±5%, 100 VDCW.	L118	198701420P5	Coil.
C148	198705108936	Capacitor, Mica Chip: 91pF ± 5%, 500 VDCW, temp coef D + 50 PPM.	L119 and	19A129569P1	Coil.
c152 and C153	19A705108P35	Hica: 82 pF ±5%, 500 VDCW, temp coef 0 +50 PPM/°C.	L120 L121	19A701420P5	Coil.
C160 and C161	192705108P30	Mics: 51 pF ±5%, 500 VDCN, temp coef 0 +50 PPM/'C.	L122 L123	19A701418p1	Coil.
C164 and C165	19A705108P22	Mics: 24 pF 15%, 500 VDCM, temp coef 0 +50 PPM/*C.	and L124 L125	19A129360P4	Coil.
C166 and C167	198705108927	Micz Chip: 39 pF ±5%, 500 VDCN, temp coef 0 + 50 PPN/°C,	and L126 L160	344A3301P1	Ceil.
C168 and C169	198705108P120	Nica chip: 1000 pF, ±5%, 100 VDCN.	and L161		
L	L	L		L	L

\*COMPONENTS ADDED, DELETED OR CHANGED BY PRODUCTION CHANGES

SYMBOL	GE PART NO.	DESCRIPTION	SYMI
1203	19A700024P37	Coil, RF: 100 uH ± 10%.	
L205			J1
		TRANSISTORS	J10
Q201	198700076P2	Silicon. NPN: sim to MMRT3904, low profile	
and Q202			010
			010
		RESISTORS	and
RLDO	198800607P270	Metal film: 27 ohms ±5%, 1/8 w.	020
R101	1988006070330	Metal film: 33 ohms ±5%, 1/8 w,	
R102	1988006079270	Metal film: 27 ohns ±5%, 1/8 w,	
8104	1988006078331	Composition: 33 ohms ± 5%, 1/2 w.	RIO
8105	1988006079300	Metal film: 330 onms 554, 1/8 w.	RIL
RIOS	1988006079331	Matal film: 330 obma 450 1/0	
R107	19870011395	Composition: 3.9 chms 4 5% 1/2 w	U100
R109	19A700112F15	Composition: 10 chms + 5% 1 v	110
R110	19A700112P13	Composition: 8.2 ohms t 5%, 1 w.	010.
R112	19A700112P13	Composition: 8.2 ohms ± 5%, 1 w.	0103
R201	198801486P101	Metal film: 100 ohms ±5%, 1/2 w.	010
and R202	1		
R203	19B800607P103	Metal film: 10K ohms ±5%, 1/8 w.	
R204	198800607P183	Hetal film: 18K ohms ±5%, 1/8 w.	WI
R205	19B800607P223	Netal film: 22K ohms ±5%, 1/8 w.	
R206	19B800607P103	Netal film: LOK ohms ±5%, 1/8 w.	
R207 and R208	19A702931P301	Hetal film: 10K ohms il%, 200 VDCW, 1/8 w.	
R209	19A705813P2	Thermistor: sim to AL03006-58.2K-97-G100.	W4
R210 and R211	1988006079472	Hetal film: 4.7% ohms 15%, 1/8 w,	
R212 and R213	19A702931F301	Hetal film: 10K ohms ±1%, 200 VDCW, 1/8 w.	
R214 and R215	19B800607P103	Metal film: 10K ohms 15%, 1/8 w.	
R216	1988006079102	Metal film: IK ohma +5% 1/8 u	W10
R217	19A700109P5	Variable, cermet: 10K ohms + 20%, 1/4 w.	W11
R218 and R219	19B801486P101	Netal film: 100 ohma 15%, 1/2 w.	W13
R220	19A702931P333	Netal film: 21.5K chms 11%, 200 VDCW, 1/8 e.	2
R221	19A702931P293	Metal film: 9090 ohms ±18, 200 VDCW, 1/8 w.	5
R223	19B800607P102	Metal film: 1K ohms ±5%, 1/8 w.	
R224	1988006079103	Metal film: 10K ohms ±5%, 1/8 w.	6
R226	19B800607P103	Metal film: 10K ohms ±5%, 1/B w.	11
8227			16
R228	198800607P102	Metal film: 1% ohms ±5%, 1/8 w.	21
R229 and R230	198800607P103	Netal film: 10K ohma ±5%, 1/8 w.	28
R233	198800607P103	Metal film: 10K ohms ±5%, 1/8 w.	29
R235	198800607P103	Metal film: 10K ohmas ±5%, 1/8 w.	30
	1		35
0101	344A3221P1	Linear: MMIC Amplifier: sim.to NPC DPC16770	37
0201	19A701789P4	Linear: Quad Op Amp; sim to LM224D.	38
			41
			45
C1	19A116708P2	Feedthru.	46
	1		50
			51
l		1	
		]	
	4		L

SYMBOL	GE PART NO.	DESCRIPTION	
11		Dave of W1	
J104	777714525	Receptacle: sim to Amphenol 82-67	
		TRANSISTORS	
Q101	19A134340P4	Silicon, MPN, VHF Amplifier: 45 w.	
and 0103	19A149632P1	Silicon, NPN, VEF Amplifier: 68 w., 12.5 volts.	
0203	19870005591	Silicon, PNP: Darlington; sim to BID-125	
-			
-144		RESISTORS	
8111	19814292284	Power: 50 chars ±5%, 150 w.	
	13/14303274	FOWER: 30 GIANS 138, 150 W.	
		INTEGRATED CIRCUITS	
U100	19A705532P2	Integrated Circuit, Linear (Positive Voltage Regulator): sim to MC78T15CT.	
U102	19A705326P1	Power Amplifier Module: 145 to 175 MHz., sim to Mitsubishi M57719	
0103	344A3219P1	Coupler, hybrid: 130 to 180 MBr, amplitude	
0104		Dalance TV.25 GB; Sim to Anaren Ro. 10262-3.	
		CABLES	
<b>U</b> 1	19890152974		
	19880056082	PF Cable	
	19A705512P3	Connector. RF SNB series: sim to AMP 228213-1	
	19A115938P1	Connector, coaxial: (BNC Series); sim to	
	]	Amphenol 31-318.	
W4	198801695611	Power Cable. Includes the following:	
	19B209268P115	Solderless terminal.	
	198209260P11	Solderless terminal.	
	19A115959P2	Wire, stranded.	
	198701503P2	Cable: battery, red.	
	19A701503P10	Cable: battery, black.	
10	198209268P116	Solderless terminal.	
W11	19880169564	Power cable: W12-W	
W13	198801739P1	Power Control cable.	
	· -		
2	19090242096	Reat sink assembly.	
7	198/023811510	0.6 x 10.	
6	713989893	Nut, hex, brass: No. 1/4-28.	
11	198702364P310	Hachine screw, TORX Drive: No. M3-0.5 x 10.	
16	19A700136P7	Insulated sleeving.	
24	1987011005	Cilp, Dop.	
22	1987023640316	Flatwasher: H3.5.	
29	19A700034P4	Nut, bez: No. M3 x 0.5MM	
30	19A700033P5	Lock washer, external tooth: No. 3.	
35	19A705469P1	Insulator Plate, TO-220.	
36	19A700068P1	Insulator, bushing.	
37	19A134455P3	Flatwasher.	
38	19880165963	Cover (see separate parts list below).	
41	198700033P6	Lockwasher, external tooth, M3.5.	
45	N405P586	Lockwasher.	
46	19A701312P4	Flatwasher: 3.2 ID.	
50	198702381P408	Tap screw, TORX Drive, M3-0.5 x 8.	
51	19A705106P1	Resistor Spacer.	
	L		

# PARTS LIST

SYMBOL	GE PART NU.	DESCRIPTION			
		COVER 198801659G3	SYMBOL	GE PART NO.	DESCRIPTION
2	19D902421P1	Power Amplifier Cover.			JACKS
, 1	193702381P522	Screw, thread forming:	J1	777714595	Receptacle: sim to Amphenol 82-97.
5	19A701365P4	Washer.	and J2		
1	19R149969P3	Shield.			
	5493477 <b>P</b> 9	Axial fan.			MISCELLANEOUS
	5493477910	Grille.	2	19D903063P1	Casting.
5	N80P13028B6	Nachine screw.	3	19D903064P1	Casting.
	N210P2186	Nachine nut.	4	19D902853G1	High Band Filter Board. See separate parts list
	19A701312P5	Flatwasher: M3.5.	5	19A702381P513	Screw, thread forming: TORX, No. M3.5 - 0.6 X 13.
	19A701863P10	Clip, loop.	6	19A702364P210	Machine screw, matric: N2.545 x 10.
	19R702364P410	Machine screw.	7	19A134455P3	Platwasher.
	198700041P28	Shell.	8	19A700032F3	Lockwasher, tooth, steel, metric: 2.5.
	19A700041P26	Contact: sim to Molex 08-50-0113.	10	19B235310P1	Nameplate.
	N405P37B6	Lock washer.	- /		
	L401P23B6	Split washer.			HIGH BAND FILTER BOARD 190902853GI
					CAPACITORS
			C301	19A116679P6R2D	6.2 pF.
			C302	19A116679F24G	24 pF.
			C303	19A116795P33G	33 pF.
			C304	19A116679P3R9D	3.9 pF.
			C305	19A116679P68J	68 pF.
			L301	19A129569P1	Coil.
L			L302	19A701418F1	Coil.
			L303	19A129569P1	Coil.
		1	L304	19A701420P5	Coil.
			L305	19A129569P1	Coil.
			L306	19A701418P1	Coil.
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			COMPO	NEINIS ADDED, D	

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## LOW PASS FILTER MCDULE 19D902856G1 ISSUE 1

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## OUTLINE DIAGRAMS

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## LOW PASS FILTER MODULE 19D902856G1

(19D902853, Sh.1, Rev. 2) (19D902854, Comp. Side, Rev. 9)



19D902797G1

(19D902797, Sh. 2, Rev. 8)

POWER AMPLIFIER ASSEMBLY 19D902797G1

(19D902797, Sh. 1, Rev. 8)

SCHEMATIC DIAGRAM



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#### **POWER AMPLIFIER ASSEMBLY** 19D902797G1

(19D902798, Sh. 1, Rev. 3)